1

Supporting Information for

CH₃NH₃PbI₃ films prepared by combining 1- and 2-step deposition: How crystal growth conditions affect properties

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Figure S1. (a) SEM image of 1 & 2-s *precursor* film prepared using x = 0.66. The sample was analysed using EDX at the points shown. Points #1 to #3 correspond to the microcrystals. Point #4 probed the mp-TiO₂ layer containing 0.66MAPbI₃ and 0.34PbI₂ (i.e., 27.0 atomic% Pb²⁺) according to Scheme 1a. For comparison PbI₂ contains 33 atomic% Pb²⁺. (b) Table of atomic % values from the points shown in (a). EDX spectra for (c) Point #1 and (d) Point #4. These data show that microcrystals (with nanocrystals at the surface) were Pb²⁺ rich compared to theory (27.0 mol.%) and Point #4.



Figure S2 Polarised light optical microscopy images (a - e) for various *final* MAPbI₃ films prepared with different solution *x* values (shown). (a) and (e) correspond to 2-s and 1-s methods, respectively. (b) to (d) were prepared using the 1 & 2-s method. (See Scheme 1c) The inset for (a) shows the analyser (A) and polariser (P) directions used.



Figure S3 Effect of *x* for the $PbI_2 + xMAI$ solutions used to prepare the precursor films on the average meso-crystal size for the *final* MAPbI₃ films shown in Fig. 1b. The combined 1 & 2-s method used x = 0.33, 0.50 and 0.66. Note that x = 0 corresponds to the 2-s method. Meso-crystals were not evident for the 1-s (x = 1.0) film.



Figure S4. Example of image used for calculation of the % coverage. This SEM image was obtained for the *final* 1 & 2-s film prepared using x = 0.66 and is taken from Fig. 1b. The yellow outline was used to delineate the crystals from the background. The automated threshold was conducted using Image J software and included only the dark black areas (pinholes). The % coverage was determined by subtracting the total pinhole area from the total area of the image and normalising the difference with the total image area.



Figure S5 (a) X-ray diffractograms for *final* MAPbI₃ films prepared using the 2-s method (x = 0) – See Scheme 1b. The immersion time was varied as shown. (b) Variation of the % of amplitude of the MAPbI₃ (110) peak with x (see text). (c) Images of the films used for (a).



Figure S6. SEM cross section of an ITO/bl-TiO₂/mp-TiO₂/MAPbI₃/Spiro-MeOTAD/Au device that contained a MAPbI₃ photoactive layer prepared using the 1 & 2-s method (x = 0.5). EDX line scanning data are shown for Pb and I. The scanning was performed perpendicular to the film surface starting from the HTM. Points #A and #B probed the compositions near the surface and deep within the photoactive layer. The atomic % values measured for Points #A and #B are shown in the table.



Figure S7 Representative SEM image for $mp-TiO_2$. The scale bar represents 100 nm. The pore size distribution is shown.



Figure S8 Expanded view of PL spectra for the final MAPbI₃ films from Fig. 5a. The values for x are shown in the legend. A calculated spectrum for x = 0.75 is shown which was obtained by using $F = 1.5 \times (0.25F_0 + 0.75F_{1.0})$ where F_o and $F_{1.0}$ are the measured fluorescence intensities for the x = 0 and 1.0 films, respectively.



Figure S9. Transient absorption spectroscopy data for mp-TiO₂/MAPbI₃/*spiro*-MeOTAD. The legend shows the values for x used for the preparation of the films. The architecture of the device used for these experiments is also shown.



Figure S10 (a) *J-V* curve for the best 1 & 2-s (x = 0.33) cells. (b) Relationship between PCE and J_{sc} for devices prepared using P3HT (black open diamonds) or spiro-OMeTAD (red open diamonds) as the HTM.

xMAI	HTM	$\mathbf{J}_{\mathbf{sc}}$	Voc	FF	PCE	Hysteresis
		(mAcm ⁻²)	(V)		(%)	(%)
0	P3HT	11.98 ± 3.02	0.83 ± 0.09	0.39 ± 0.09	4.23 ± 1.14	15.1 ± 1.9
0.33		9.98 ± 1.14	0.84 ± 0.06	0.37 ± 0.05	3.04 ± 0.44	8.75 ± 0.88
0.50		7.85 ± 0.44	0.83 ± 0.03	0.36 ± 0.04	2.35 ± 0.45	6.60 ± 0.73
0.66		6.73 ± 1.07	0.81 ± 0.07	0.39 ± 0.05	2.17 ± 0.68	4.33 ± 0.52
1.0		6.38 ± 0.8	0.68 ± 0.17	0.41 ± 0.09	1.90 ± 0.95	2.42 ± 0.38
0	SPIRO	24.2 ± 0.21	0.85 ± 0.02	0.51 ± 0.04	10.32 ± 0.86	16.3 ± 1.86
0.33		21.9 ± 0.50	0.86 ± 0.01	0.46 ± 0.02	8.64 ± 0.55	8.40 ± 0.70
0.50		18.8 ± 1.5	0.86 ± 0.01	0.44 ± 0.05	7.04 ± 0.63	7.43 ± 0.73
0.66		16.3 ± 1.4	0.86 ± 0.01	0.44 ± 0.02	6.17 ± 0.97	5.25 ± 0.76
1.0		13.6 ± 0.5	0.84 ± 0.01	0.46 ± 0.02	$5.19\ \pm 0.34$	3.35 ± 1.42

Table S1: Photovoltaic performance data for perovskite devices measured using the forward $scan.^{a}$

^{*a*} The \pm values are standard deviations.